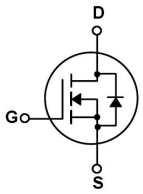
TO-262 N MOS N-CHANNEL MOSFET in a TO-262 Plastic Package.

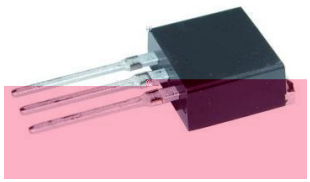
, ,

Low gate charge, low crss, fast switching.

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.



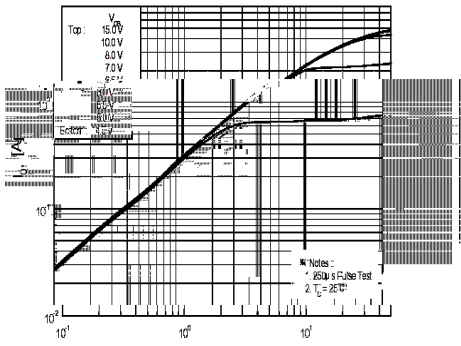


PIN1 G PIN 2 D PIN 3 S

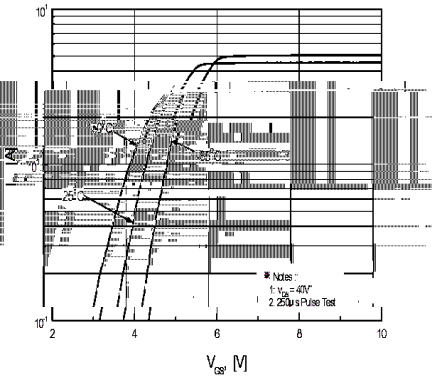
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	I_D(Tc=25)	2.0	A
Drain Current	I_D(Tc=100)	1.3	A
Drain Current - Pulsed	I_{DM}	6.0	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	120	mJ
Repetitive Avalanche Energy	E_{AR}	5.4	mJ
Avalanche Current	I_{AR}	2.0	A
Power Dissipation	P_D(Tc=25)	54	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	
Thermal Resistance Junction-case	R	˜	ๅ

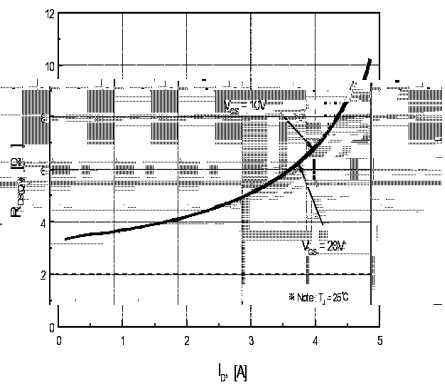
ID - VDS



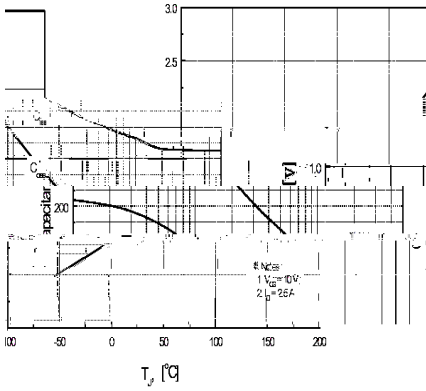
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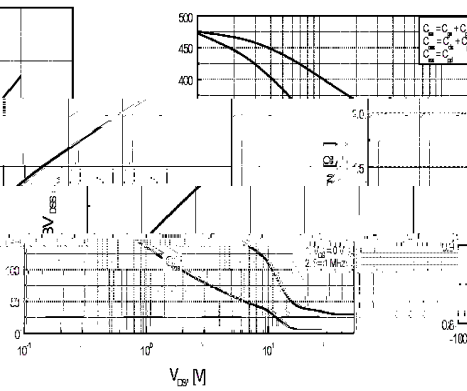
RDS(ON) - ID



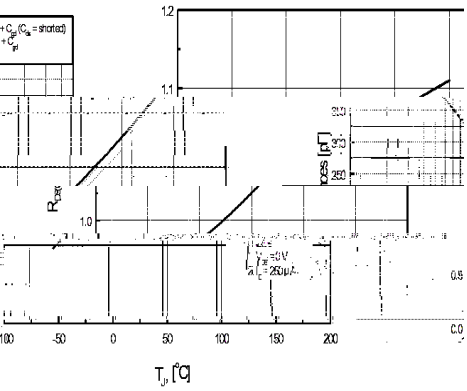
RDS(ON) - TJ



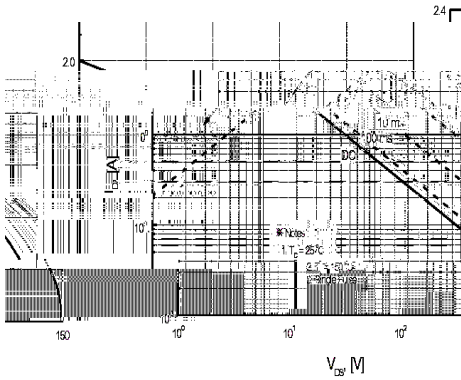
Ciss, Coss, Crss - VDS



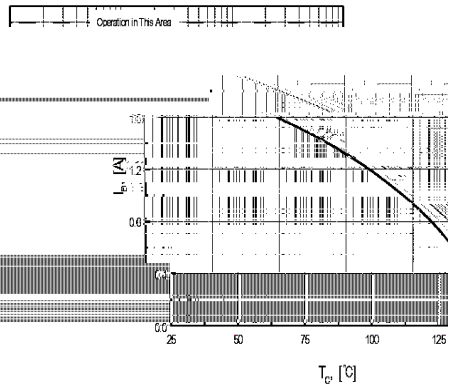
BVDSS - TJ

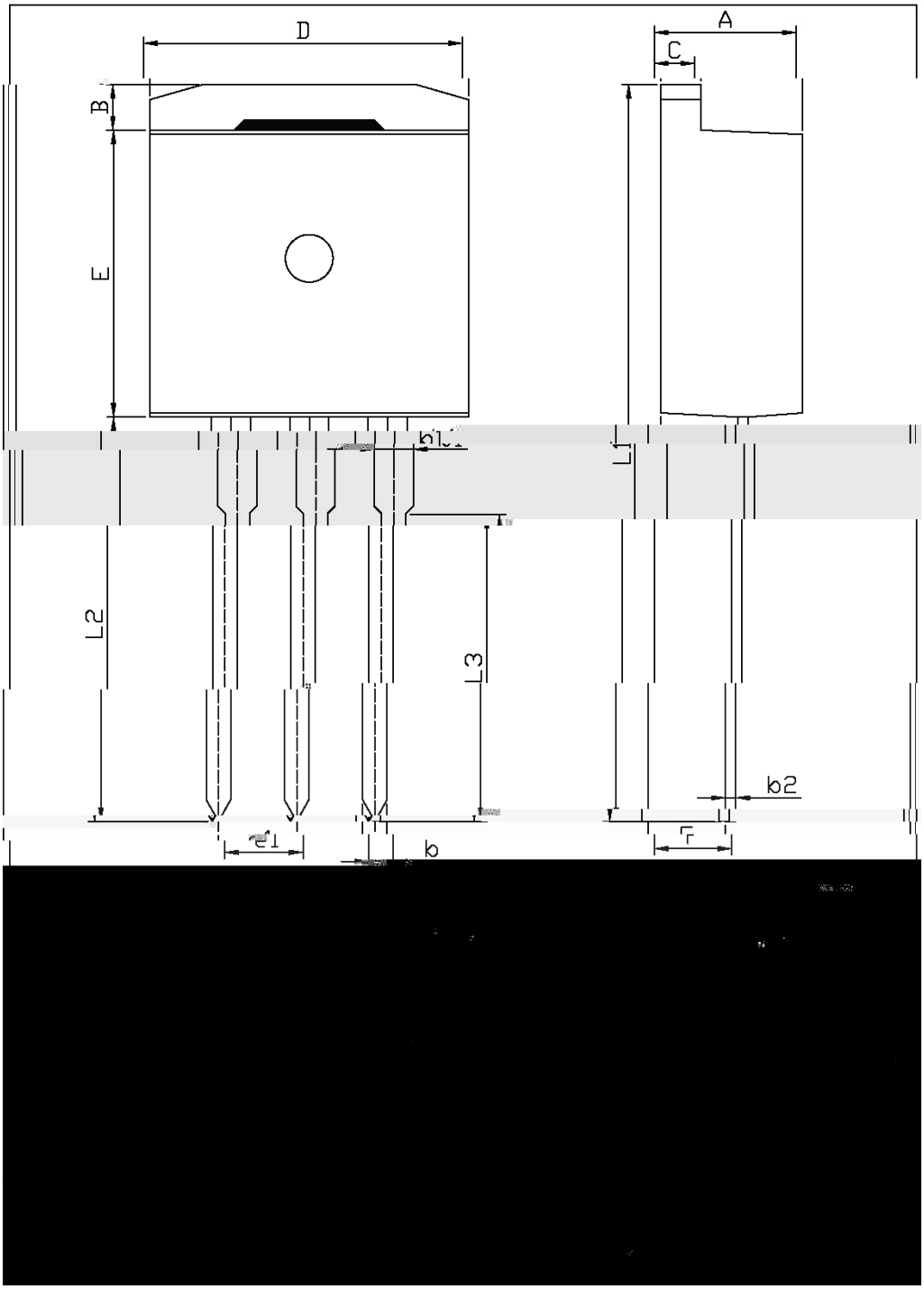


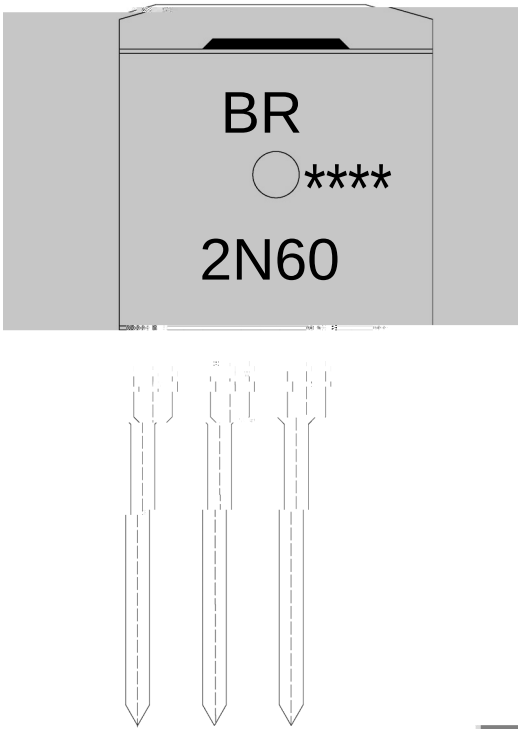
ID - TC



ID - VDS




D
A
C
B
E
L1
L2
L3
b2
b



BR

2N60

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Note:

BR:	Company Code
2N60:	Product Type.
****:	Lot No. Code, code change with Lot No.